

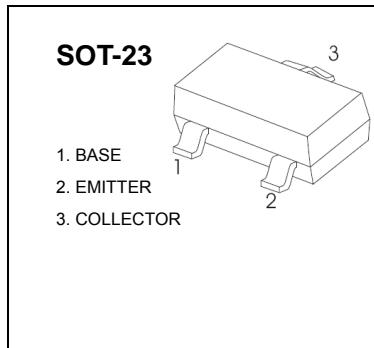
## TRANSISTOR (NPN)

### FEATURES

- Complementary to S9015

**MARKING: J6**

**MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$  unless otherwise noted)**



Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{CEO}$	Collector-Emitter Voltage	45	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_c$	Collector Current -Continuous	0.1	A
$P_c$	Collector Power Dissipation	0.2	W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C= 100\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C= 0.1\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=50\text{ V}, I_E=0$			0.1	$\mu\text{ A}$
Collector cut-off current	$I_{CEX}$	$V_{CE}=35\text{V}, V_x =-3\text{V}$			50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}= 3\text{V}, I_C=0$			0.1	$\mu\text{ A}$
DC current gain	$h_{FE}$	$V_{CE}=5\text{V}, I_C= 1\text{mA}$	200		1000	
Collector-emitter saturation voltage	$V_{CE}(\text{sat})$	$I_C=100 \text{ mA}, I_B= 5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE}(\text{sat})$	$I_C=100 \text{ mA}, I_B= 5\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C= 10\text{mA}$ $f=30\text{MHz}$	150			MHz

### CLASSIFICATION OF $h_{FE}$

Rank	L	H
Range	200-450	450-1000



